



STBV32

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

Ordering Code	Marking	Package / Shipment
STBV32	BV32	TO-92 / Bulk
STBV32-AP	BV32	TO-92 / Ammopack

- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED

APPLICATIONS:

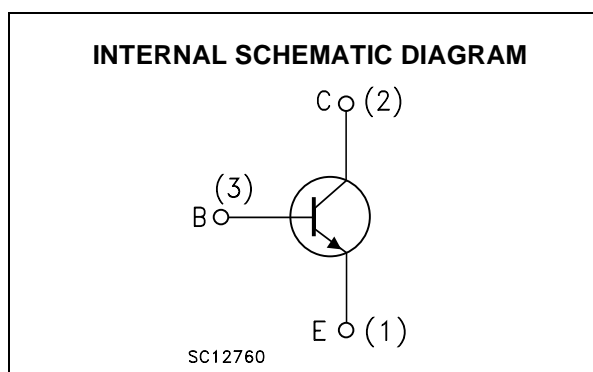
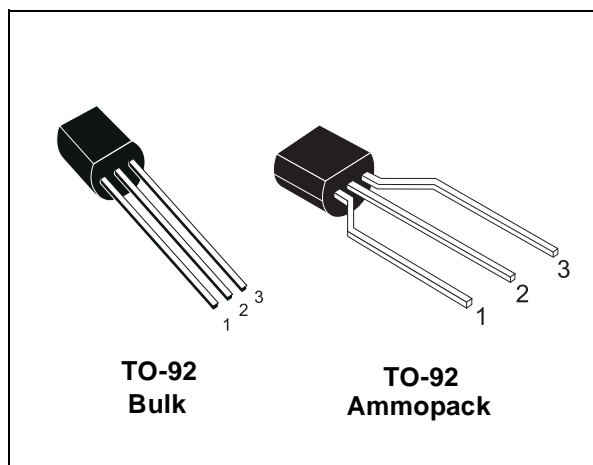
- COMPACT FLUORESCENT LAMPS (CFLS)

DESCRIPTION

The device is manufactured using High Voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability.

It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA.

The STBV series is designed for use in Compact Fluorescent Lamps.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	700	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	400	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0, I_B < 0.5$ A, $t_p < 10$ ms)	$V_{(BR)EBO}$	V
I_C	Collector Current	1	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	3	A
I_B	Base Current	0.5	A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	1.5	A
P_{tot}	Total Dissipation at $T_{amb} = 25$ °C	1.1	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

STBV32

THERMAL DATA

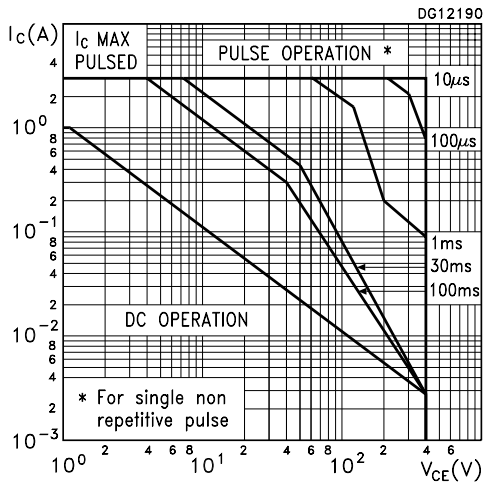
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	112	°C/W
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ELECTRICAL CHARACTERISTICS ($T_j = 25\text{ °C}$ unless otherwise specified)

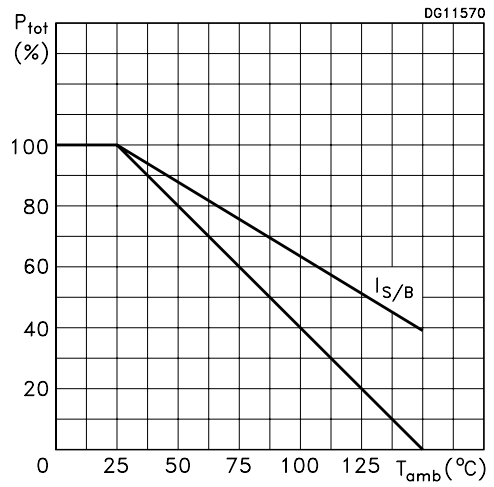
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEV}	Collector Cut-off Current ($V_{BE} = -1.5\text{ V}$)	$V_{CE} = 700\text{ V}$ $V_{CE} = 700\text{ V}$ $T_j = 125\text{ °C}$			1 5	mA mA
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 10\text{ mA}$	9		18	V
$V_{CEO(sus)}^*$	Collector-Emitter Sustaining Voltage ($I_B = 0$)	$I_C = 10\text{ mA}$	400			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 0.5\text{ A}$ $I_B = 100\text{ mA}$ $I_C = 1\text{ A}$ $I_B = 250\text{ mA}$ $I_C = 1.5\text{ A}$ $I_B = 500\text{ mA}$			0.5 1 1.5	V V V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 0.5\text{ A}$ $I_B = 100\text{ mA}$ $I_C = 1\text{ A}$ $I_B = 250\text{ mA}$			1 1.2	V V
h_{FE}^*	DC Current Gain	$I_C = 0.5\text{ A}$ $V_{CE} = 2\text{ V}$ $I_C = 1\text{ A}$ $V_{CE} = 2\text{ V}$	8 5		35 25	
t_r t_s t_f	RESISTIVE LOAD Rise Time Storage Time Fall Time	$I_C = 1\text{ A}$ $V_{CC} = 125\text{ V}$ $I_{B1} = -I_{B2} = 200\text{ mA}$ $t_p = 25\text{ }\mu\text{s}$ (See Figure 1)			1 4 0.7	μs μs μs
t_s	INDUCTIVE LOAD Storage Time	$I_C = 1\text{ A}$ $V_{clamp} = 300\text{ V}$ $I_{B1} = 200\text{ mA}$ $V_{BE(off)} = -5\text{ V}$ $L = 50\text{ mH}$ $R_{BB} = 0$ (See Figure 2)		0.8		μs

* Pulsed: Pulse duration = 300 μs , duty cycle = 1.5 %.

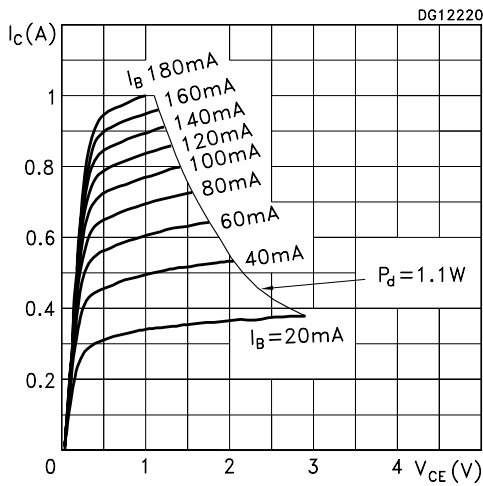
Safe Operating Area



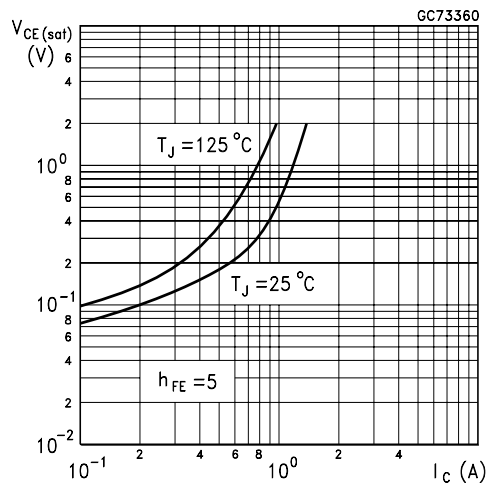
Derating Curve



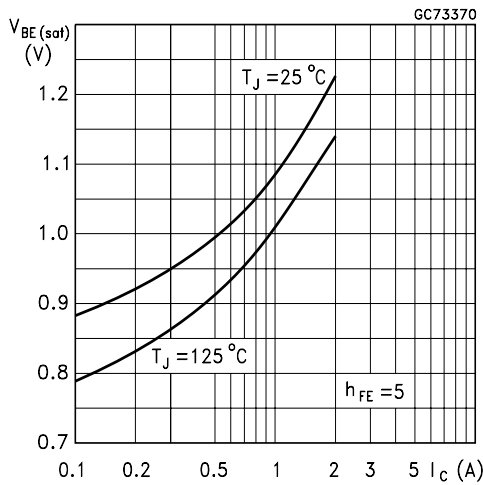
Output characteristics



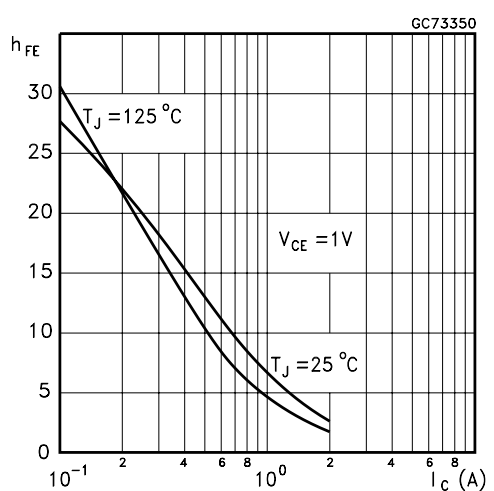
Collector-Emitter Saturation Voltage



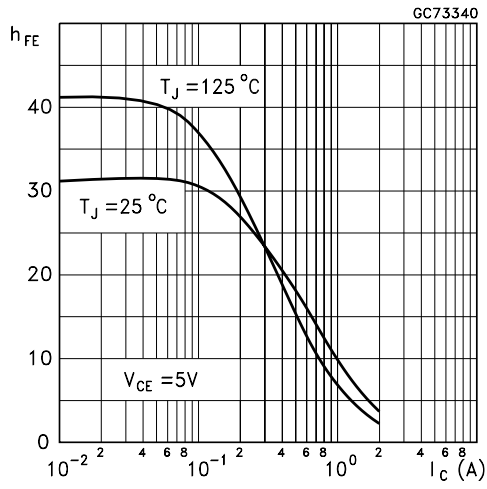
Base-Emitter Saturation Voltage



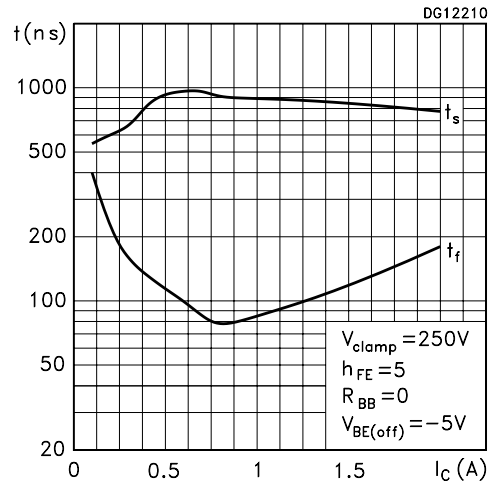
DC Current Gain



DC Current Gain



Inductive Load Switching Times



Reverse Biased Safe Operating Area

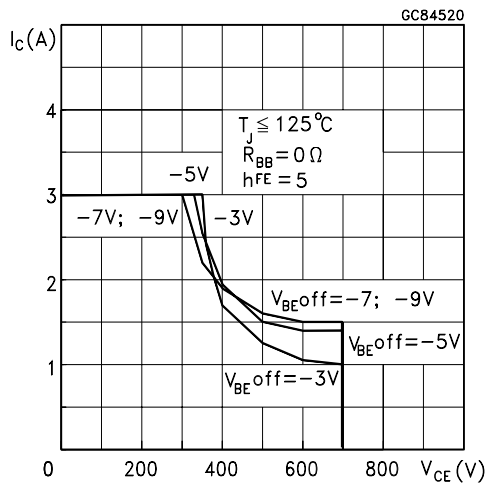


Figure 1: Resistive Load Switching Test Circuit

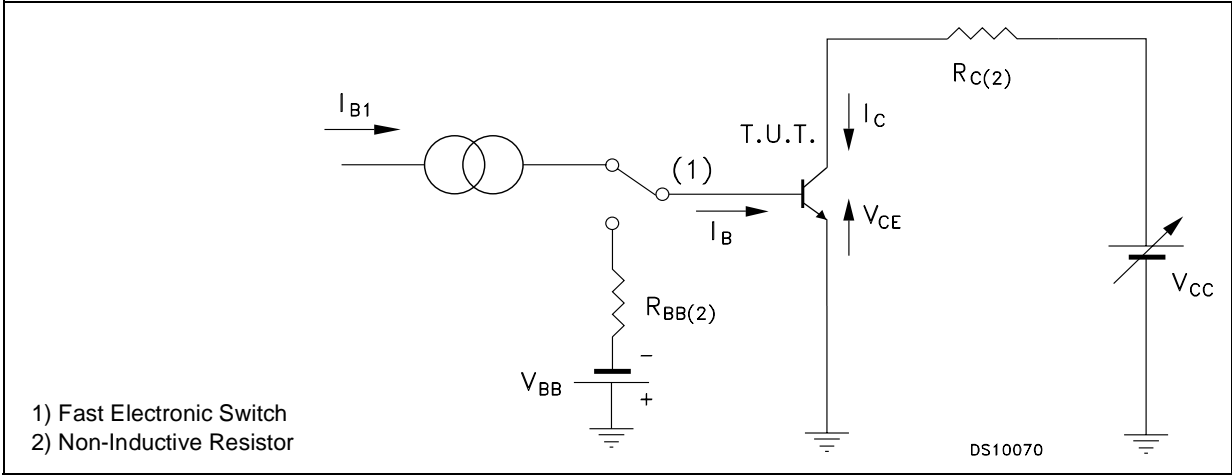
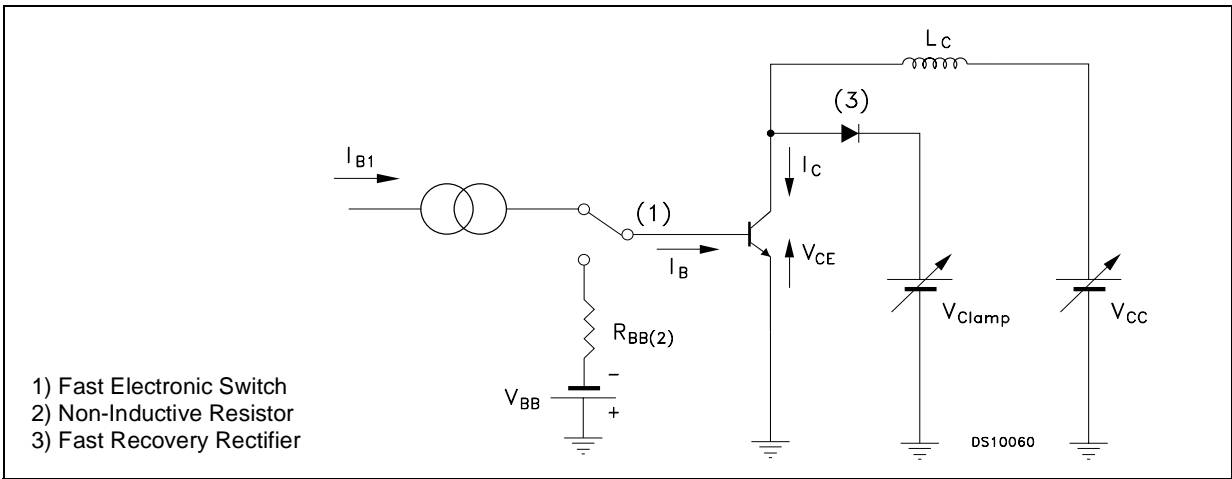
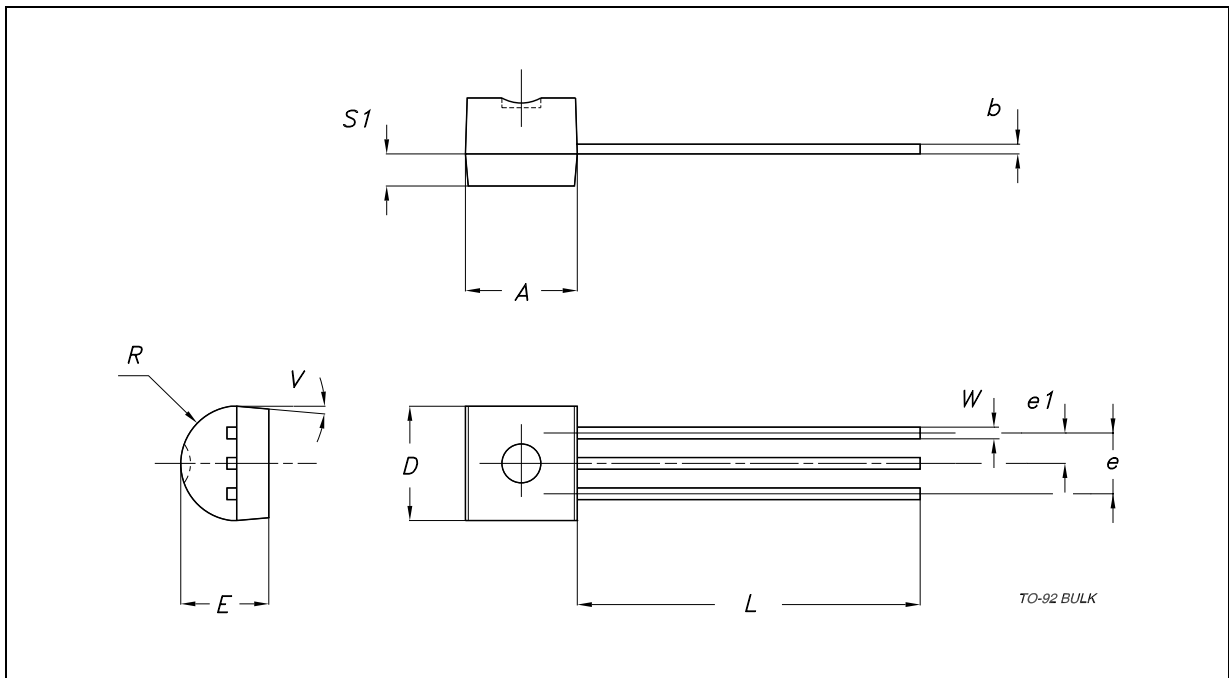


Figure 2: Inductive Load Switching Test Circuit



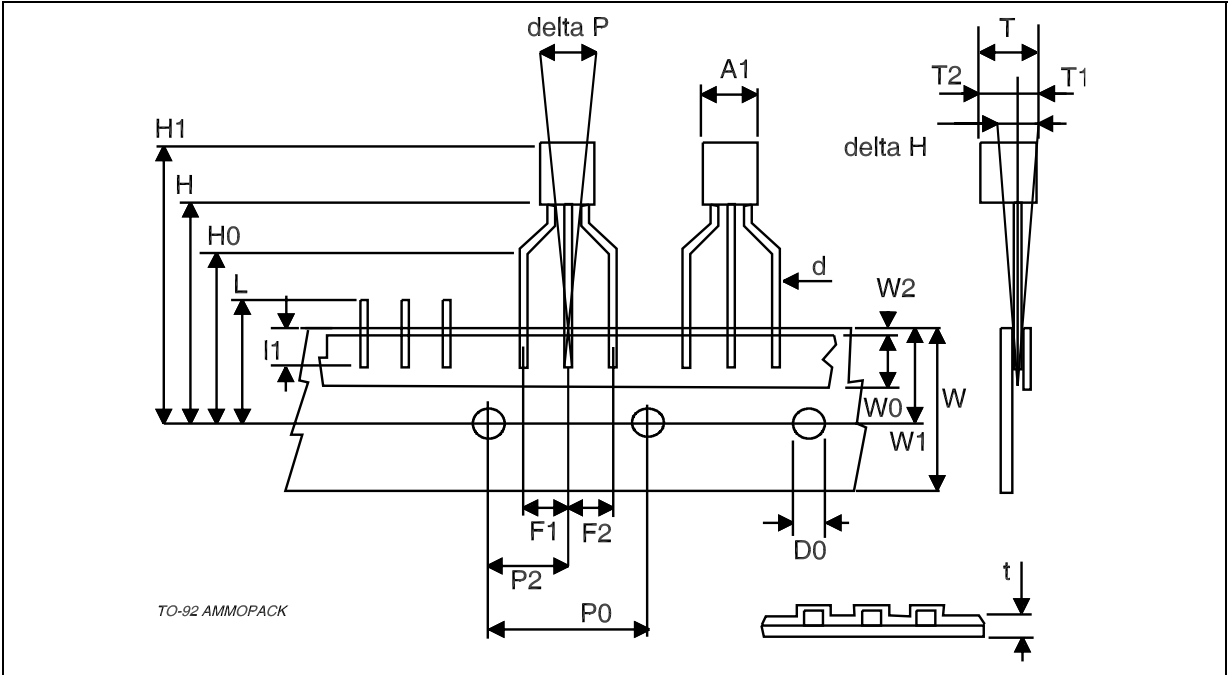
TO-92 BULK SHIPMENT MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.95	0.170		0.195
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.195
E	3.30		3.94	0.130		0.155
e	2.41		2.67	0.095		0.105
e1	1.14		1.40	0.045		0.055
L	12.70		15.49	0.500		0.610
R	2.16		2.41	0.085		0.095
S1	0.92		1.52	0.036		0.060
W	0.41		0.56	0.016		0.022
V		5°			5°	



TO-92 AMMOPACK SHIPMENT (Suffix “-AP”) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A1			4.80			0.189
T			3.80			0.150
T1			1.60			0.063
T2			2.30			0.091
d			0.48			0.019
P0	12.50	12.70	12.90	0.492	0.500	0.508
P2	5.65	6.35	7.05	0.222	0.250	0.278
F1, F2	2.44	2.54	2.94	0.096	0.100	0.116
delta H	-2.00		2.00	-0.079		0.079
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.70	6.00	6.30	0.224	0.236	0.248
W1	8.50	9.00	9.25	0.335	0.354	0.364
W2			0.50			0.020
H	18.50		20.50	0.728		0.807
H0	15.50	16.00	16.50	0.610	0.630	0.650
H1			25.00			0.984
D0	3.80	4.00	4.20	0.150	0.157	0.165
t			0.90			0.035
L			11.00			0.433
l1	3.00			0.118		
delta P	-1.00		1.00	-0.039		0.039



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